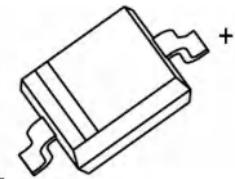




迈拓电子
MAITUO ELECTRONIC

BAV19W~BAV21W SWITCHING DIODE



FEATURES

- Low Reverse Current
- Surface Mount Package Ideally Suited for Automatic Insertion
- Fast Switching Speed
- For General Purpose Switching Applications

MARKING: BAV19W A8

BAV20W T2

BAV21W T3

SOD - 123

MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

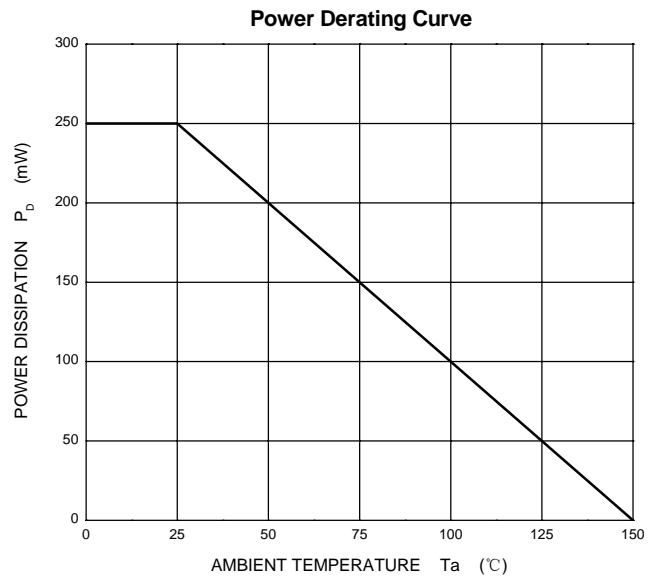
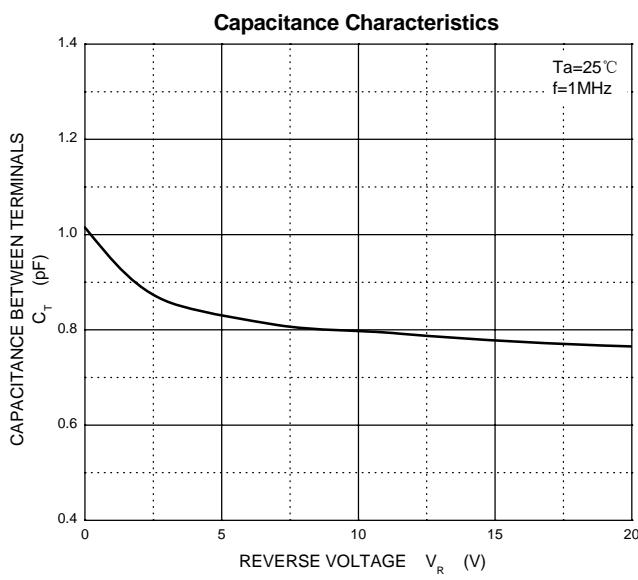
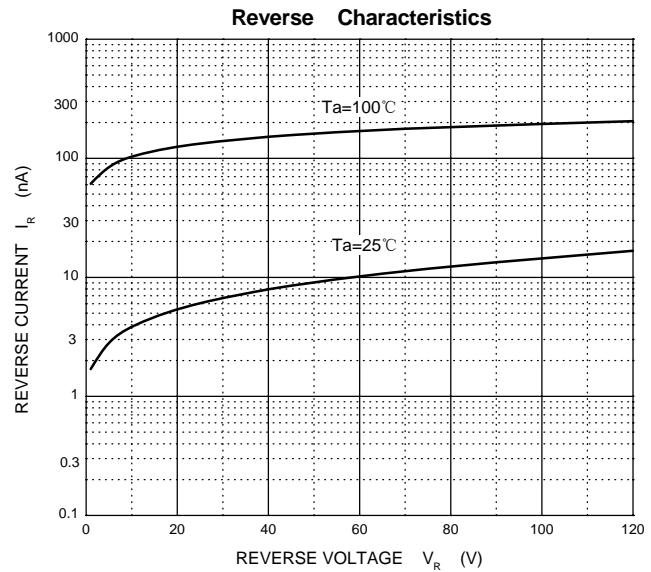
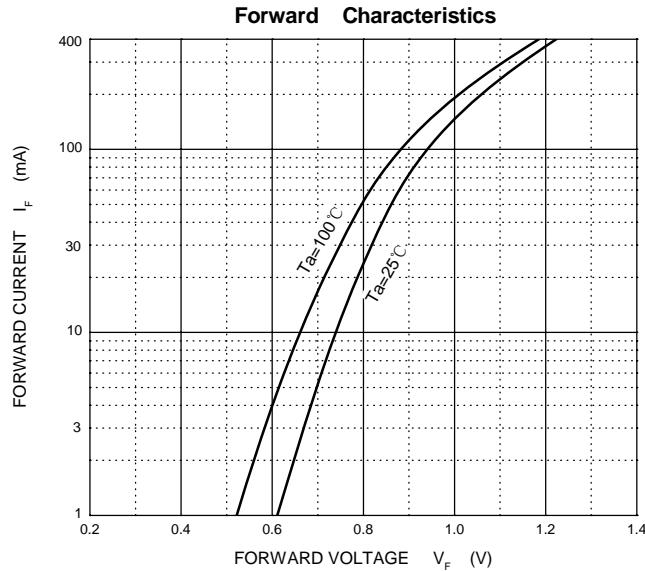
Symbol	Parameter	Value			Unit
		BAV19W	BAV20W	BAV21W	
V_{RM}	Non-Repetitive Peak Reverse Voltage	120	200	250	V
V_{RRM}	Peak Repetitive Reverse Voltage	100	150	200	V
V_{RWM}	Working Peak Reverse Voltage				
$V_{R(\text{RMS})}$	RMS Reverse Voltage	71	106	141	V
I_o	Average Rectified Output Current	200			mA
I_{FSM}	Non-repetitive Peak Forward Surge Current @ $t=8.3\text{ms}$	2.0			A
P_D	Power Dissipation	250			mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	500			°C/W
T_j	Junction Temperature	150			°C
T_{stg}	Storage Temperature	-55~+150			°C

ELECTRICAL CHARACTERISTICS($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions		Min	Typ	Max	Unit
Reverse current	I_R	$V_R=100\text{V}$	BAV19W			0.1	uA
		$V_R=150\text{V}$	BAV20W			0.1	
		$V_R=200\text{V}$	BAV21W			0.1	
Forward voltage	V_F	$I_F=100\text{mA}$				1	V
		$I_F=200\text{mA}$				1.25	
Total capacitance	C_{tot}	$V_R=0\text{V}, f=1\text{MHz}$				5	pF
Reverse recovery time	t_{rr}	$I_F= I_R =30\text{mA}, I_{rr}=0.1*I_R, R_L=100\Omega$				50	ns



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PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

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